WHAT IS CLAIMED IS:

1. A semiconductor device, comprising a three dimensional object, comprising at least one multilayer structure formed by a process for preparing a multilayer structure, comprising:

a substrate;

a coupling layer deposited on the substrate; and

a dielectric layer deposited on the coupling layer,

wherein shear strength of the dielectric layer is increased by a factor of at least about 2 in the presence of the coupling layer compared to a multilayer structure without the coupling layer, comprising:

(a) coating a substrate with a composition that forms the coupling layer to form a first coated substrate; and

(b) coating the first coated substrate with a composition that forms the dielectric layer.